This question paper contains 2 printed pages] Roll No. S. No. of Question Paper: 1522 E Unique Paper Code : 222261 : Electronics II : Analog Circuits (ELPT-202) Name of the Paper : B.Sc. Physical Sciences Name of the Course : **П** Semester Maximum Marks: 75 Duration: 3 Hours (Write your Roll No. on the top immediately on receipt of this question paper.) Attempt Five questions in all. Ouestion No. 1 is compulsory.  $3 \times 5 = 15$ Attempt any five of the following: 1. Give one application each of a transistor in CE, CB, CC configuration. Write any three basic characteristics of ideal Operational Amplifier. (b) Discuss advantages of a bridge rectifier over a centre tap full wave rectifier. (c) Explain how do the I-V characteristics of an ideal diode resemble those of a switch? (d)(e) What is thermal runaway? How can it be prevented? Draw the circuit of a clipper and briefly describe its working. (f)Explain the terms I<sub>CEO</sub> and I<sub>CBO</sub>. Which of them is greater? (g) What are the sources of leakage current in BJTs? (h)

2.	(a)	Draw the block diagram of a regulated power supply and explain the function of each
		block in detail.
	(b)	Explain the working of a half wave rectifier and derive the expression for its ripple
		factor 5
3.	(a)	Explain the terms $\alpha$ and $\beta$ for a transistor. Find the relation between the two. 5
	(b)	Explain working of an n-p-n BJT configured in CE mode as an amplifier and thus describe
		its static input and output characteristics.
4	(a)	Explain with the help of a circuit diagram the working of a class B push pull amplifier.
		What are its advantages over class A amplifier?
	(b)	Classify amplifiers with respect to operating point selection.
5.	(a)	Derive the expression of voltage gain for an inverting op-amp with a suitable diagram. 8
	(b)	Draw the circuit diagram of an op-amp configured as an integrator and obtain an expression
	•	for output voltage.
6.	(a)	Explain the working and characteristics of an n-channel enhancement type MOSFET with
		the help of a well-labelled diagram.
	(b)	List the advantages of a FET over BJT.
7.	Wri	te short notes on any two of the following: $2\times7\frac{1}{2}$
•	(a)	Early effect
	(b)	Formation of depletion layer in PN junction
	(c)	JFET.

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